

MAX22290/MAX22291

Product Highlights

- AEC-Q100 Qualification for /V Devices
- Reinforced Galvanic Isolation for Digital Signals
 - 8-SOIC with 4mm of Creepage and Clearance
 - Withstands 3kV_{RMS} for 60s (V_{ISO})
 - Continuously withstands 445V_{RMS} (V_{IOWM})
 - Withstands ±10kV Surge between GNDA and GNDB with 1.2/50µs Waveform
 - High CMTI (50kV/µs, typ)
- Low Power Consumption
 - 0.78mW per Channel at 1Mbps with V_{DD} = 1.8V
 - 1.47mW per Channel at 1Mbps with $V_{DD_{-}} = 3.3V$
 - 3.28mW per Channel at 100Mbps with V_{DD} = 1.8V
- Low Propagation Delay and Low Jitter
 - Up to 200Mbps Maximum Data Rate
 - Low Propagation Delay 7ns (typ) at $V_{DD_{-}}$ = 3.3V
 - Clock Jitter RMS 7.5ps (typ)
- Safety Regulatory Approvals
 - UL According to UL1577
 - cUL According to CSA Bulletin 5A
 - VDE 0884-11 Reinforced Insulation (Pending)

Key Applications

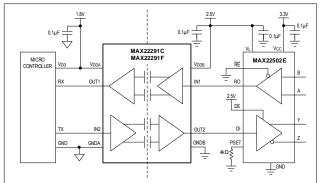
- Automotive
 - Hybrid Electric Vehicle
 - · Chargers
 - Battery Management Systems (BMS)
 - Inverters

The MAX22290/MAX22291 is a family of 2-channel reinforced, fast, low-power digital galvanic isolators using Maxim's proprietary process technology. All devices feature reinforced isolation for a withstand voltage rating of $3kV_{RMS}$ for 60 seconds. Both automotive and general-purpose devices are rated for operation at ambient temperatures of -40°C to +125°C.

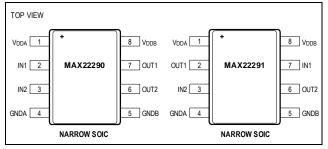
Devices with /V suffix are AEC-Q100 qualified. See the <u>Ordering Information</u> table for all automotive grade part numbers.

- Industrial
 - Isolated SPI
 - Isolated RS-232, RS-485/RS-422, CAN
 - Fieldbus Communications
 - Motor Drive

Simplified Application Diagram



Pin Configurations



These devices transfer digital signals between circuits with different power domains, using as little as 0.78mW per channel at 1Mbps (1.8V supply). The low-power feature reduces system dissipation, increases reliability, and enables compact designs.

The devices are available with a maximum data rate of 25Mbps or 200Mbps, and with outputs that are either default high or default low. They feature low propagation delay and low clock jitter, which reduces system latency.

Independent 1.71V to 5.5V supplies on each side of the isolator also make the devices suitable for use as level translators.

The MAX22290 features two channels transferring data in the same direction. The two channels of the MAX22291 transfer data in opposite directions, and this makes the MAX22291 ideal for isolating the Tx and Rx lines of a transceiver.

Ordering Information appears at end of data sheet.

19-101159; Rev 2; 10/21

Reinforced, Fast, Low-Power, Two-Channel Digital Isolators

Absolute Maximum Ratings

V _{DDA} to GNDA0.3V to +6V	
V _{DDB} to GNDB0.3V to +6V	
IN_ on Side A to GNDA0.3V to +6V	
IN_ on Side B to GNDB0.3V to +6V	
OUT_ on Side A to GNDA0.3V to (V_DDA + 0.3V)	
OUT_ on Side B to GNDB0.3V to (V_DDB + 0.3V)	
Short-Circuit Continuous Current	
OUT_ on Side A to GNDA±30mA	

OUT_ on Side B to GNDB ±30mA
Continuous Power Dissipation ($T_A = +70^{\circ}C$)
Narrow SOIC (derate 5.79mW/°C above +70°C) 462.96mW
Temperature Ratings
Operating Temperature Range40°C to +125°C
Maximum Junction Temperature+150°C
Storage Temperature Range60°C to +150°C
Lead Temperature (soldering, 10s)+300°C
Soldering Temperature (reflow)+260°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Information

8 NARROW SOIC

Package Code	S8MS+24				
Outline Number	<u>21-0041</u>				
Land Pattern Number	<u>90-0096</u>				
THERMAL RESISTANCE, FOUR-LAYER BOARD					
Junction-to-Ambient (θ _{JA})	172.8°C/W				
Junction-to-Case Thermal Resistance (θ_{JC})	67.6°C/W				

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to <u>www.maximintegrated.com/thermal-tutorial</u>.

For the latest package outline information and land patterns (footprints), go to <u>www.maximintegrated.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Electrical Characteristics

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, C_L = 15\text{pF}, T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted}. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}\text{C}, \text{ unless otherwise noted}.) (Notes 1, 3)$

PARAMETER	SYMBOL	CON	DITIONS	MIN	TYP	MAX	UNITS	
SUPPLY VOLTAGE	·			•				
•	V _{DDA}	Relative to GNDA		1.71		5.5		
Supply Voltage	V _{DDB}	Relative to GNDB		1.71		5.5	V	
Undervoltage-Lockout Threshold	V _{UVLO} _	V _{DD} _ rising		1.5	1.6	1.66	V	
Undervoltage-Lockout Threshold Hysteresis	V _{UVLO_HYST}				45		mV	
MAX22290 SUPPLY CU	RRENT (Note 2)							
			$V_{DDA} = 5V$		0.31	0.57		
		500kHz square	$V_{DDA} = 3.3V$		0.30	0.56		
		wave, $C_L = 0pF$	V _{DDA} = 2.5V		0.30	0.56		
Cide A Consels Consent			$V_{DDA} = 1.8V$		0.29	0.41		
Side A Supply Current	I _{DDA}		V _{DDA} = 5V		2.38	3.25	mA	
		50MHz square	V _{DDA} = 3.3V		2.32	3.18		
		wave, $C_L = 0pF$	$V_{DDA} = 2.5V$		2.29	3.14		
			V _{DDA} = 1.8V		2.22	2.89		
				$V_{DDB} = 5V$		0.60	1.11	
	500kHz square	V _{DDB} = 3.3V		0.59	1.10	1		
		wave, $C_L = 0pF$	V _{DDB} = 2.5V		0.59	1.09	mA	
			V _{DDB} = 1.8V		0.58	1.06		
Side B Supply Current	IDDB	IDDB 50MHz square wave, C _L = 0pF	V _{DDB} = 5V		3.02	3.80		
			V _{DDB} = 3.3V		2.12	2.80		
			V _{DDB} = 2.5V		1.74	2.35		
			V _{DDB} = 1.8V		1.42	1.95		
MAX22291 SUPPLY CU	RRENT (Note 2)	ł		I				
			V _{DDA} = 5V		0.46	0.84		
		500kHz square	V _{DDA} = 3.3V		0.45	0.83		
		wave, $C_L = 0pF$	$V_{DDA} = 2.5V$		0.44	0.83		
			$V_{DDA} = 1.8V$		0.44	0.74	-	
Side A Supply Current	I _{DDA}		$V_{DDA} = 5V$		2.65	3.50	mA	
		50MHz square	V _{DDA} = 3.3V		2.18	2.95	_	
			$V_{DDA} = 2.5V$		1.98	2.72		
			V _{DDA} = 1.8V		1.80	2.40	1	
			$V_{\text{DDB}} = 5V$		0.46	0.84		
		500kHz square	$V_{\text{DDB}} = 3.3 V$		0.45	0.83		
		wave, $C_L = 0pF$	$V_{\text{DDB}} = 2.5V$		0.44	0.83	- mA	
Side B Supply Current	IDDB		$V_{\text{DDB}} = 1.8V$		0.44	0.74		
	50MHz square	$V_{DDB} = 5V$		2.65	3.50	1		
		wave, $C_L = 0pF$	$V_{\text{DDB}} = 3.3V$		2.18	2.95	1	

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, C_L = 15\text{pF}, T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes 1, 3)}$

PARAMETER	SYMBOL	COND	CONDITIONS		TYP	MAX	UNITS
			V _{DDB} = 2.5V		1.98	2.72	
			V _{DDB} = 1.8V		1.80	2.40	
LOGIC INTERFACE (IN_	, OUT_)		•				-
	N	$2.25V \le V_{DD_{-}} \le 5.5V$	1	0.7 x V _{DD}			V
	VIH	1.71V ≤ V _{DD_} < 2.25V		0.75 x V _{DD}			V
		$2.25V \le V_{DD_{-}} \le 5.5V$				0.8	V
Input Low Voltage	VIL	1.71V ≤ V _{DD} _ < 2.25	ŠV.			0.7	v
		MAX2229_B/E			410		
Input Hysteresis	V _{HYS}	MAX2229_C/F			80		mV
Input Pullup Current	I _{PU}	MAX2229_B/C		-10	-5	-1.5	μA
Input Pulldown Current	I _{PD}	MAX2229_E/F		1.5	5	10	μA
Input Capacitance	C _{IN}	f _{SW} = 1MHz			2		pF
Output Voltage High	V _{OH}	I _{OUT} = -4mA source		V _{DD_} - 0.4			V
Output Voltage Low	V _{OL}	I _{OUT} = 4mA sink	I _{OUT} = 4mA sink			0.4	V

Dynamic Characteristics MAX2229_C/F

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, C_L = 15pF, T_A = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ unless otherwise noted}$. Typical values are at $V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}C, \text{ unless otherwise noted}$. (Notes 2, 4)

PARAMETER	SYMBOL	CO	NDITIONS	MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	СМТІ	$IN_ = GND_ or V_{I}$	DD_ (Note 5)		50		kV/µs
Maximum Data Rate	DP	$2.25V \le V_{DD_{-}} \le 5$.5V	200			Mbps
	DR _{MAX}	$1.71V \le V_{DD_{-}} < 2$.25V	150			Mibbs
Minimum Pulse Width	D\\/	$2.25V \le V_{DD_{-}} \le 5$.5V			5	
	PW _{MIN}	1.71V ≤ V _{DD} _ < 2	.25V			6.67	ns
			$4.5 \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{V}$	4.4	6.2	9.5	
	-		$3.0V \le V_{DD_{-}} \le 3.6V$	4.8	7.0	11.2	
			2.25V ≤ V _{DD} _≤ 2.75V	5.3	8.3	14.7	
Propagation Delay			1.71V ≤ V _{DD} _ ≤ 1.89V	7.1	12.3	22.1	- ns
(<u>Figure 1</u>)			$4.5 V \le V_DD_ \le 5.5 V$	4.6	6.5	9.9	
			$3.0V \le V_{DD_{-}} \le 3.6V$	5.0	7.3	11.6	
^t PHL	$\begin{array}{c} \text{IN_to OUT_,} \\ \text{C}_{L} = 15\text{pF} \end{array}$	2.25V ≤ V _{DD} _ ≤ 2.75V	5.4	8.5	14.9		
			1.71V ≤ V _{DD} _ ≤ 1.89V	7.2	12.1	21.8	
Pulse Width Distortion			$4.5 V \leq V_{DD} \leq 5.5 V$		0.4	2	
	dth Distortion PWD t _{PLH}	t _{PLH} - t _{PHL}	$3.0V \le V_{DD_{-}} \le 3.6V$		0.4	2	ns
			2.25V ≤ V _{DD} _ ≤ 2.75V		0.3	2	

PARAMETER	SYMBOL	CO	NDITIONS	MIN	TYP	MAX	UNITS	
			1.71V ≤ V _{DD} _ ≤ 1.89V		0.0	2		
		$4.5V \le V_{DD} \le 5.8$	5V			3.7		
		$3.0V \le V_{DD} \le 3.6$	6V			4.7		
	^t SPLH	$2.25V \le V_{DD} \le 2$	2.75V			6.9		
Propagation Delay		1.71V ≤ V _{DD} _ ≤ 1	.89V			12.1		
Skew Part-to-Part (Same Channel)		$4.5V \le V_{DD} \le 5.5$	5V			4.0	ns	
(Came Chamler)		$3.0V \le V_{DD} \le 3.6$	6V			4.9		
	^t SPHL	$2.25V \le V_{DD} \le 2$	2.75V			7.0		
		1.71V ≤ V _{DD} ≤ 1				11.8	1	
Propagation Delay	tSCSLH	1.71V ≤ V _{DD} ≤ 5	5.5V			2		
Skew Channel-to- Channel (Same Direction) (<u>Figure 1</u>)	t _{SCSHL}	1.71V ≤ V _{DD} _ ≤ 5	5.5V			2	ns	
Propagation Delay	t _{SCOLH}	1.71V ≤ V _{DD} ≤ 5.5V			2			
Skew Channel-to- Channel (Opposite Direction)	^t SCOHL	1.71V ≤ V _{DD} ≤ 5.5V				2	ns	
Peak Eye Diagram Jitter	tJIT(PK)	200Mbps			100		ps	
Clock Jitter RMS	tJCLK(RMS)	500kHz clock inpu	ut, rising/falling edges		7.5		ps	
			$4.5V \le V_{DD_{-}} \le 5.5V$			0.8		
			$3.0V \le V_{DD} \le 3.6V$			1.1		
Rise Time (<u>Figure 1</u>) t _R	t _R	$C_L = 5pF$	2.25V ≤ V _{DD} _ ≤ 2.75V			1.5	ns	
			1.71V ≤ V _{DD} _ ≤ 1.89V			2.4	-	
			$4.5V \le V_{DD_{-}} \le 5.5V$			1		
			$3.0V \le V_{DD_{-}} \le 3.6V$			1.4]	
Fall Time (<u><i>Figure 1</i></u>)	t _F	$C_L = 5pF$	$2.25V \le V_{DD_{-}} \le 2.75V$			1.9	ns	
			1.71V ≤ V _{DD} _ ≤ 1.89V			3		

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, C_L = 15\text{pF}, T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted}. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}\text{C}, \text{ unless otherwise noted}.) (Notes 2, 4)$

Dynamic Characteristics MAX2229_B/E

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, C_L = 15\text{pF}, T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted}. Typical values are at V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}\text{C}, \text{ unless otherwise noted}.) (Notes 2, 4)$

PARAMETER	SYMBOL	CON	DITIONS	MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	CMTI	$IN_=GND_or V_D$	_{D_} (Note 5)		50		kV/µs
Maximum Data Rate	DR _{MAX}			25			Mbps
Minimum Pulse Width	PW _{MIN}					40	ns
Glitch Rejection				10	17	29	ns
			$4.5V \le V_{DD_{-}} \le 5.5V$	16.7	22.6	30.7	
			$3.0V \le V_{DD} \le 3.6V$	17.0	23.4	32.2	
	t _{PLH}	IN_ to OUT_, C _L = 15pF	$2.25V \le V_{DD_{-}} \le$ 2.75V	17.7	24.8	35.3	
Propagation Delay			1.71V ≤ V _{DD} _≤ 1.89V	19.6	28.8	42.8	ns
(<u>Figure 1</u>)			$4.5 V \leq V_{DD_} \leq 5.5 V$	16.4	22.7	32.1	115
			$3.0V \le V_{DD_{-}} \le 3.6V$	16.8	23.5	33.8	
	t _{PHL}	IN_ to OUT_, C _L = 15pF	2.25V ≤ V _{DD} _ ≤ 2.75V	17.3	24.8	36.7	
			1.71V ≤ V _{DD} _ ≤ 1.89V	19.0	28.4	43.7	
			$4.5 V \leq V_{DD_} \leq 5.5 V$		0.1	4	
			$3.0V \le V_{DD_{-}} \le 3.6V$		0.1	4	
Pulse Width Distortion	PWD t _{PLH} - t _{PHL}	t _{PLH} - t _{PHL}	2.25V ≤ V _{DD} _≤ 2.75V		0.0	4	ns
			1.71V ≤ V _{DD} _ ≤ 1.89V		0.4	4	
		$4.5V \le V_{DD_{-}} \le 5.5V$				14.0	
	4	$3.0V \le V_{DD_{-}} \le 3.6$	V			13.8	
	^t SPLH	$2.25V \le V_{DD} \le 2.25V$	75V			15.2	
Propagation Delay		1.71V ≤ V _{DD} ≤ 1.89V				21.9]
Skew Part-to-Part (Same Channel)		$4.5V \le V_{DD_{-}} \le 5.5$	V			13.0	- ns
· · · · ·	4	$3.0V \le V_{DD_{-}} \le 3.6$	V			13.5	
	^t SPHL	$2.25 V \le V_{DD} \le 2.25 V$	75V			15.4	
		$1.71V \le V_{DD_{-}} \le 1.3$	89V			21.4	
Propagation Delay	^t SCSLH	$1.71V \le V_{DD_{-}} \le 5.1$	5V			4	
Skew Channel-to- Channel (Same Direction) (<i>Figure 1</i>)	t _{SCSHL}	1.71V ≤ V _{DD} _ ≤ 5.	5V			4	ns
Propagation Delay	^t SCOLH	1.71V ≤ V _{DD} ≤ 5.	5V			4	
Skew Channel-to- Channel (Opposite Direction)	tSCOHL	1.71V ≤ V _{DD} _ ≤ 5.				4	ns
Peak Eye Diagram Jitter	t _{JIT(PK)}	25Mbps			250		ps
	-JII (PK)		4.5V ≤ V _{DD} ≤ 5.5V			0.8	
	4	0 5=5	$3.0V \le V_{DD} \le 3.6V$			1.1	-
Rise Time (<u>Figure 1</u>)	t _R	C _L = 5pF	2.25V ≤ V _{DD} _ ≤ 2.75V			1.5	ns

 $(V_{DDA} - V_{GNDA} = 1.71V \text{ to } 5.5V, V_{DDB} - V_{GNDB} = 1.71V \text{ to } 5.5V, C_L = 15\text{pF}, T_A = -40^{\circ}\text{C} \text{ to } +125^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = 3.3V, V_{DDB} - V_{GNDB} = 3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes 2, 4)}$

PARAMETER	SYMBOL	C	ONDITIONS	MIN	ТҮР	MAX	UNITS
			1.71V ≤ V _{DD} _ ≤ 1.89V			2.4	
			$4.5 \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{V}$			1	
Fall Time (<u>Figure 1</u>) t _F			$3.0V \le V_{DD_{-}} \le 3.6V$			1.4	
	$C_L = 5pF$	2.25V ≤ V _{DD} _≤ 2.75V			1.9	ns	
			1.71V ≤ V _{DD} _ ≤ 1.89V			3	

Note 1: General purpose devices are 100% production tested at $T_A = +25$ °C. Specifications over temperature are guaranteed by design and characterization. Automotive devices are 100% production tested at $T_A = +25$ °C and $T_A = +125$ °C.

Note 2: Not production tested. Guaranteed by design and characterization.

Note 3: All currents into the device are positive. All currents out of the device are negative. All voltages are referenced to their respective ground (GNDA or GNDB), unless otherwise noted.

- Note 4: All measurements taken with V_{DDA} = V_{DDB}, unless otherwise noted.
- **Note 5:** CMTI is the maximum sustainable common-mode voltage slew rate while maintaining the correct output. CMTI applies to both rising and falling common-mode voltage edges. Tested with the transient generator connected between GNDA and GNDB (V_{CM} = 1000V).

ESD Protection

PARAMETER	SYMBOL	CONDITIONS	MIN TYP MAX		UNITS	
500		Human Body Model All Pins	ody Model All Pins ±3			
ESD		IEC 61000-4-2 Contact, GNDB to GNDA		±6		kV

Test Circuit and Timing Diagram

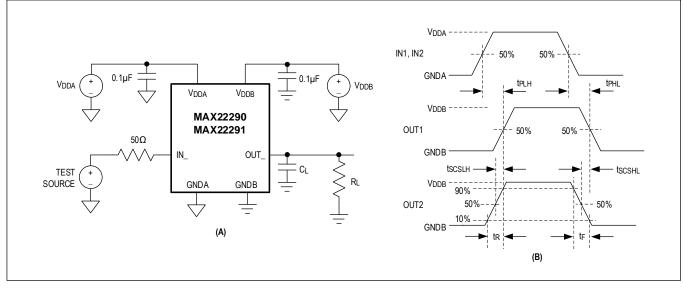


Figure 1. Test Circuit (A) and Timing Diagram (B)

Table 1. Insulation Characteristics

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS
Partial Discharge Test Voltage	V _{PR}	Method B1 = V _{IORM} x 1.875 (t = 1s, partial discharge < 5pC)	1182	V _P
Maximum Repetitive Peak Isolation Voltage	VIORM	(Note 6)	630	VP
Maximum Working Isolation Voltage	V _{IOWM}	Continuous RMS voltage (Note 6)	445	V _{RMS}
Maximum Transient Isolation Voltage	V _{IOTM}	t = 1s (Note 6)	4242	VP
Maximum Withstanding Isolation Voltage	V _{ISO}	$f_{SW} = 60Hz$, duration = 60s (Notes 6, 7)	3000	V _{RMS}
Maximum Surge Isolation Voltage	V _{IOSM}	Reinforced Insulation, test method per IEC 60065, $V_{TEST} = 1.6 \times V_{IOSM} = 10000 V_{PEAK}$ (Notes 6, 9)	6250	V _P
		$V_{IO} = 500V, T_A = 25^{\circ}C$	> 10 ¹²	
Isolation Resistance	R _{IO}	$V_{IO} = 500V, 100^{\circ}C \le T_A \le 125^{\circ}C$	> 10 ¹¹	Ω
		V _{IO} = 500V, T _S = 150°C	> 10 ⁹	
Barrier Capacitance Side A to Side B	C _{IO}	f _{SW} = 1MHz (Note 8)	1.5	pF
Minimum Creepage Distance	CPG		4	mm
Minimum Clearance Distance	CLR		4	mm
Internal Clearance		Distance through insulation	0.021	mm
Comparative Tracking Index	СТІ	Material Group II (IEC 60112)	> 400	
Climate Category			40/125/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	

Note 6: V_{ISO} , V_{IOTM} , V_{IOWM} , V_{IORM} and V_{IOSM} are defined by the IEC 60747-5-5 standard.

Note 7: Product is qualified at V_{ISO} for 60s and 100% production tested at 120% of V_{ISO} for 1s.

Note 8: Capacitance is measured with all pins on field-side and logic-side tied together.

Note 9: Devices are immersed in oil during surge characterization.

Safety Regulatory Approvals

UL

The MAX22290/MAX22291 are certified under UL1577. For more details, refer to File E351759.

Rated up to $3000V_{RMS}$ isolation voltage for single protection.

cUL (Equivalent to CSA notice 5A)

The MAX22290/MAX22291 are certified up to 3000V_{RMS} for single protection. For more details, refer to File E351759.

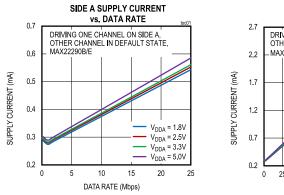
VDE (Pending)

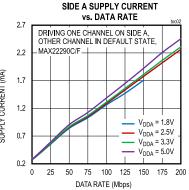
The MAX22290/MAX22291 are certified to DIN VDE V 0884-11: 2017-1. Reinforced Insulation, Maximum Transient Isolation Voltage 4242V_{PK}, Maximum Repetitive Peak Isolation Voltage 630V_{PK}.

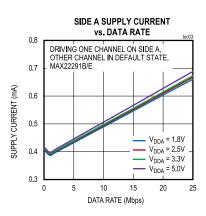
These couplers are suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

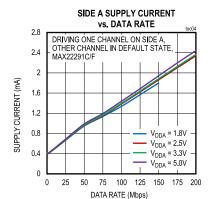
Typical Operating Characteristics

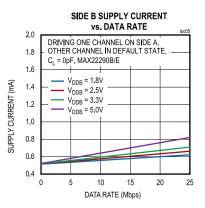
(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)

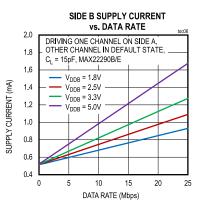




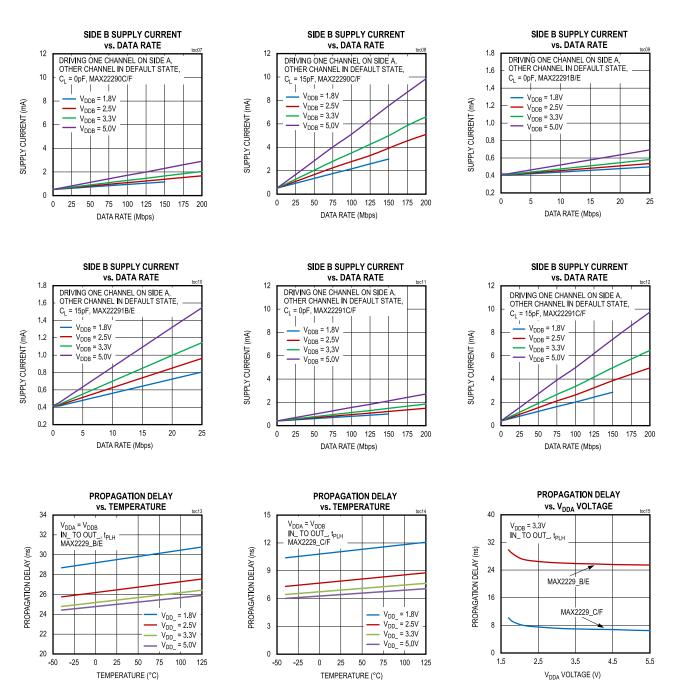






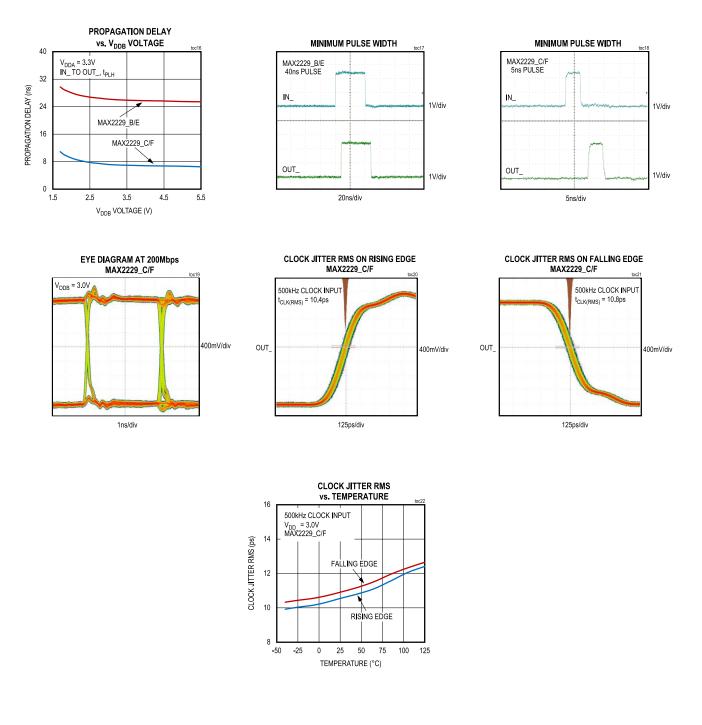


Reinforced, Fast, Low-Power, Two-Channel Digital Isolators



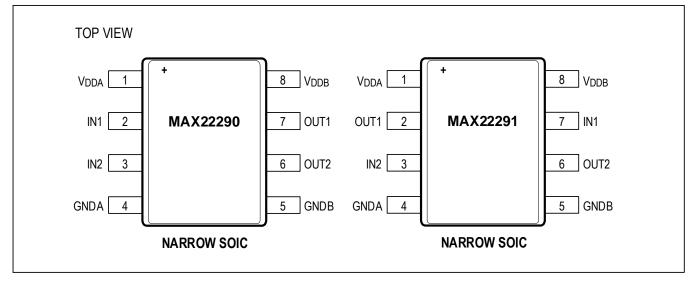
 $(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}C$, unless otherwise noted.)

Reinforced, Fast, Low-Power, Two-Channel Digital Isolators



 $(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25^{\circ}C$, unless otherwise noted.)

Pin Configurations

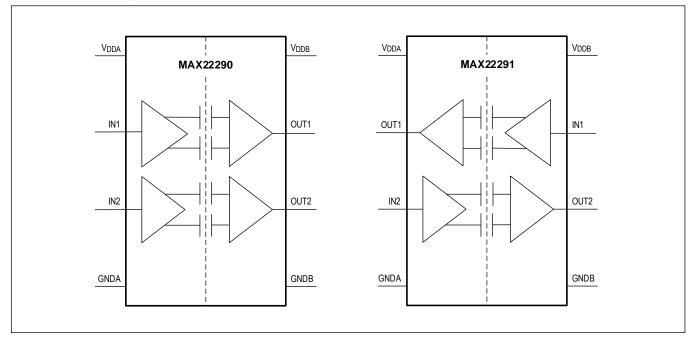


Pin Description

PIN			FUNCTION				
MAX22290	MAX22291	NAME	FUNCTION				
1	1	V _{DDA}	Power Supply Input for Side A. Bypass V_{DDA} to GNDA with a 0.1µF ceramic capacitor as close as possible to the pin.				
2	—	IN1	Logic Input 1 on Side A				
_	2	OUT1	Logic Output 1 on Side A				
3	3	IN2	Logic Input 2 on Side A				
4	4	GNDA	Ground Reference for Side A				
5	5	GNDB	Ground Reference for Side B				
6	6	OUT2	Logic Output 2 on Side B				
7	—	OUT1	Logic Output 1 on Side B				
_	7	IN1	Logic Input 1 on Side B				
8	8	V _{DDB}	Power Supply Input for Side B. Bypass V_{DDB} to GNDB with a 0.1µF ceramic capacitor as close as possible to the pin.				

Reinforced, Fast, Low-Power, Two-Channel Digital Isolators

Functional Diagrams



Detailed Description

The MAX22290/MAX22291 is a family of 2-channel reinforced digital isolators. The devices have an isolation rating of 3kV_{RMS}. The MAX22290/MAX22291 family offers two unidirectional channel configurations to accommodate any 2-channel design.

The MAX22290 features two channels transferring digital signals in one direction for applications such as isolated digital I/O. The MAX22291 has one channel to transmit data in one direction and the other channel to transmit in the opposite direction, making it ideal for applications such as isolated RS232 or RS485 communication.

The devices are available in an 8-pin narrow-body SOIC package with 4mm creepage and clearance and are rated up to 3kV_{RMS}. This family of digital isolators offers the low-power operation, high electromagnetic interference (EMI) immunity, and stable temperature performance through Maxim's proprietary process technology. The devices isolate different ground domains and block high-voltage/high-current transients from sensitive or human interface circuitry.

The devices are available with a maximum data rate of either 25Mbps (B/E versions) or 200Mbps (C/F versions). The MAX2229_B/C feature default-high outputs. The MAX2229_E/F feature default-low outputs. The default is the state the output assumes when the input is not powered or if the input is an open circuit. The devices have two supply inputs (V_{DDA} and V_{DDB}) that independently set the logic levels on either side of the device. V_{DDA} and V_{DDB} are referenced to GNDA and GNDB, respectively. The MAX2229_1 family also features a refresh circuit to ensure output accuracy when an input remains in the same state indefinitely.

Digital Isolation

The MAX22290/MAX22291 provide reinforced galvanic isolation for digital signals that are transmitted between two ground domains. The devices withstand differences of up to $3kV_{RMS}$ for up to 60 seconds, and up to $630V_{PEAK}$ of continuous isolation.

AEC-Q100 Qualification

Devices with /V suffix are AEC-Q100 qualified. See the <u>Ordering Information</u> table for all automotive grade part numbers.

Level Shifting

The wide supply voltage range of both V_{DDA} and V_{DDB} allows the devices to be used for level translation in addition to isolation. V_{DDA} and V_{DDB} can be independently set to any voltage from 1.71V to 5.5V. The supply voltage sets the logic level on the corresponding side of the isolator.

Unidirectional Channels

Each channel of these devices is unidirectional; it only passes data in one direction, as indicated in the *Functional Diagrams*. Each device features two unidirectional channels that operate independently with guaranteed data rates from DC up to 25Mbps (B/E versions), or from DC to 200Mbps (C/F versions). The output driver of each channel is push-pull, eliminating the need for pullup resistors. The outputs can drive both TTL and CMOS logic inputs.

Startup and Undervoltage Lockout

The V_{DDA} and V_{DDB} supplies are both internally monitored for undervoltage conditions. Undervoltage events can occur during power-up, power-down, or during normal operation due to a sagging supply voltage. When an undervoltage condition is detected on either supply, all outputs go to their default states regardless of the state of the inputs as seen in <u>Table 2</u>. <u>Figure 2</u>–Figure 5 shows the behavior of the outputs during power-up and power-down.

Table 2. MAX22290/MAX22291 Output Behavior During Undervoltage Condition

V _{IN_}	V _{DDA}	V _{DDB}	V _{OUTA}	V _{OUTB}
1	Powered	Powered	High	High
0	Powered	Powered	Low	Low
Х	Undervoltage	Powered	Default	Default
Х	Powered	Undervoltage	Default	Default

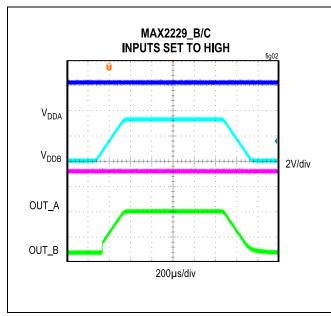


Figure 2. Undervoltage Lockout Behavior MAX2229_ B/C Input High

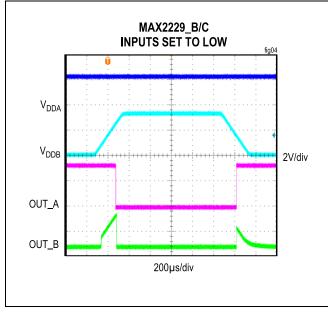


Figure 4. Undervoltage Lockout Behavior MAX2229_ B/C Input Low

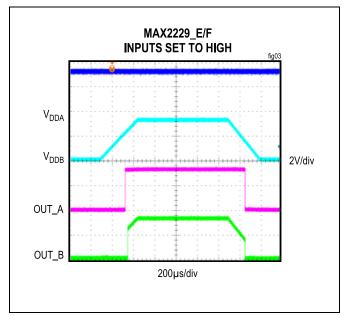


Figure 3. Undervoltage Lockout Behavior MAX2229_ E/F Input High

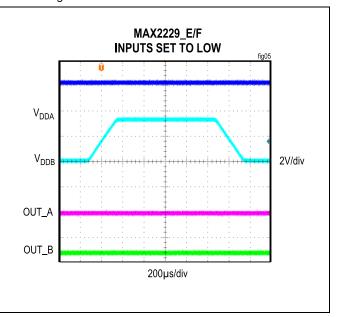


Figure 5. Undervoltage Lockout Behavior MAX2229_ E/F Input Low

Safety Limits

Damage to the IC can result in a low-resistance path to the ground or to the supply and, without current limiting, the MAX22290/MAX22291 can dissipate excessive amounts of power. Excessive power dissipation can damage the die and result in damage to the isolation barrier, potentially causing downstream issues. <u>Table 3</u> shows the safety limits for the MAX22290/MAX22291.

The maximum safety temperature (T_S) for the device is the 150°C maximum junction temperature specified in the <u>Absolute</u> <u>Maximum Ratings</u>. The power dissipation (P_D) and junction-to-ambient thermal impedance (θ_{JA}) determine the junction temperature. Thermal impedance values (θ_{JA} and θ_{JC}) are available in the <u>Package Information</u> section and power dissipation calculations are discussed in the <u>Calculating Power Dissipation</u> section. Calculate the junction temperature (T_J) as:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$

<u>Figure 6</u> and <u>Figure 7</u> show the thermal derating curves for safety limiting the power and the current of the devices. Ensure that the junction temperature does not exceed 150°C.

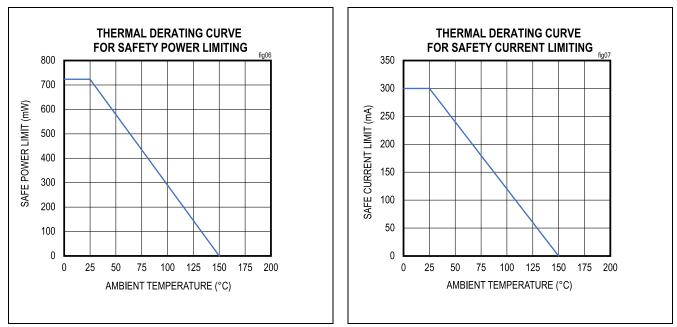


Figure 6. Thermal Derating Curve for Safety Power Limiting

Figure 7. Thermal Derating Curve for Safety Current Limiting

Table 3. Safety Limiting Values for the MAX22290/MAX22291

PARAMETER	SYMBOL	TEST CONDITIONS	MAX	UNIT
Safety Current on Any Pin (No Damage to Isolation Barrier)	۱ _S	T _J = 150°C, T _A = 25°C	300	mA
Total Safety Power Dissipation	PS	T _J = 150°C, T _A = 25°C	723.38	mW
Maximum Safety Temperature	Τ _S		150	°C

Applications Information

Power-Supply Sequencing

The MAX22290/MAX22291 do not require special power-supply sequencing. The logic levels are set independently on either side by V_{DDA} and V_{DDB} . Each supply can be present over the entire specified range regardless of the level or presence of the other supply.

Power-Supply Decoupling

To reduce ripple and the chance of introducing data errors, bypass V_{DDA} and V_{DDB} with 0.1µF low-ESR ceramic capacitors to GNDA and GNDB, respectively. Place the bypass capacitors as close to the power-supply input pins as possible.

Layout Considerations

The PCB designer should follow some critical recommendations to get the best performance from the design.

- Keep the input/output traces as short as possible. To keep signal paths low inductance, avoid using vias.
- Have a solid ground plane underneath the high-speed signal layer.
- Keep the area underneath the MAX22290/MAX22291 free from ground and signal planes. Any galvanic or metallic connection between Side A and Side B defeats the isolation.

Calculating Power Dissipation

The required current for a given supply (V_{DDA} or V_{DDB}) can be estimated by summing the current required for each channel. The supply current for a channel depends on whether the channel is an input or an output, the channel's data rate, and the capacitive or resistive load if it is an output. The typical current for input or output at any data rate can be estimated from the graphs in <u>Figure 8</u> and <u>Figure 9</u>. Note that the data in <u>Figure 8</u> and <u>Figure 9</u> are extrapolated from the supply current measurements in a typical operating condition.

The total current for a single channel is the sum of the no-load current (shown in <u>Figure 8</u> and <u>Figure 9</u>), which is a function of voltage and data rate, and the load current, which depends on the type of load. Current into a capacitive load is a function of the load capacitance, the switching frequency, and the supply voltage.

$$I_{CL} = C_L \times f_{SW} \times V_{DD}$$

where:

 I_{CL} is the current required to drive the capacitive load.

C_L is the load capacitance on the isolator's output pin.

f_{SW} is the switching frequency (bits per second/2).

 V_{DD} is the supply voltage on the output side of the isolator.

Current into a resistive load depends on the load resistance, the supply voltage, and the average duty cycle of the data waveform. The DC load current can be conservatively estimated by assuming the output is always high.

$$I_{RL} = V_{DD} \div R_L$$

where:

 I_{RL} is the current required to drive the resistive load.

 V_{DD} is the supply voltage on the output side of the isolator.

R_L is the load resistance on the isolator's output pin.

Example (shown in <u>Figure 10</u>): A MAX22291C/F is operating with $V_{DDA} = 2.5V$, $V_{DDB} = 3.3V$, channel 1 operating at 100Mbps with a 15pF capacitive load, and channel 2 operating at 20Mbps and 50% duty cycle with a 10k Ω resistive load. See <u>Table 4</u> and <u>Table 5</u> for V_{DDA} and V_{DDB} supply-current calculation worksheets.

V_{DDA} must supply:

- Channel 1 is an output channel operating at 2.5V and 100Mbps, consuming 0.84mA, estimated from Figure 9.
- Channel 2 is an input channel operating at 2.5V and 20Mbps, consuming 0.35mA, estimated from Figure 8.
- I_{CL} on Channel 1 for 15pF capacitor at 2.5V and 100Mbps is 1.875mA.

Total current for side A = 0.84mA + 0.35mA + 1.875mA = 3.065mA (typ)

V_{DDB} must supply:

- Channel 1 is an input channel operating at 3.3V and 100Mbps, consuming 1.16mA, estimated from Figure 8.
- Channel 2 is an output channel operating at 3.3V and 20Mbps, consuming 0.41mA, estimated from Figure 9.
- I_{RL} on Channel 2 for 10kΩ resistor switching at 50% duty cycle and at 3.3V is 0.165mA.

Total current for side B = 1.16mA + 0.41mA + 0.165mA = 1.735mA (typ)

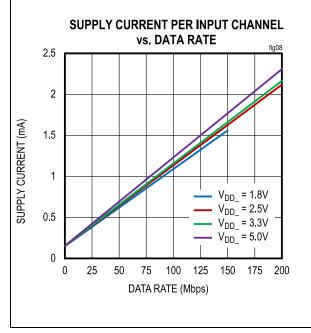


Figure 8. Supply Current per Input Channel (Estimated)

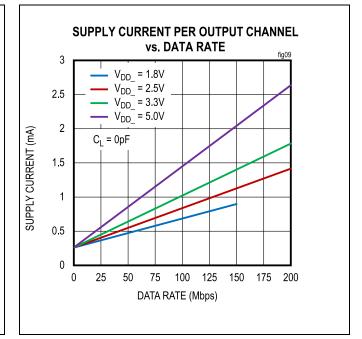


Figure 9. Supply Current per Output Channel (Estimated)

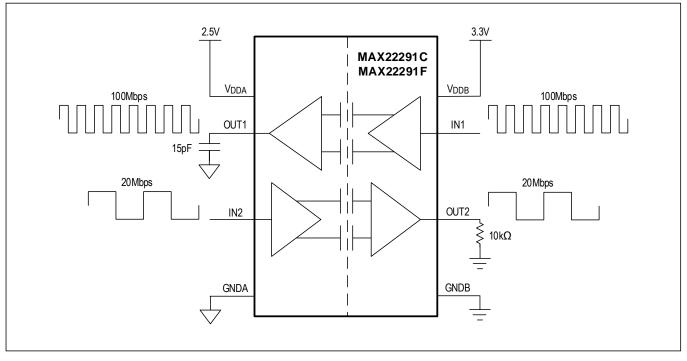


Figure 10. Example Circuit for Supply Current Calculation

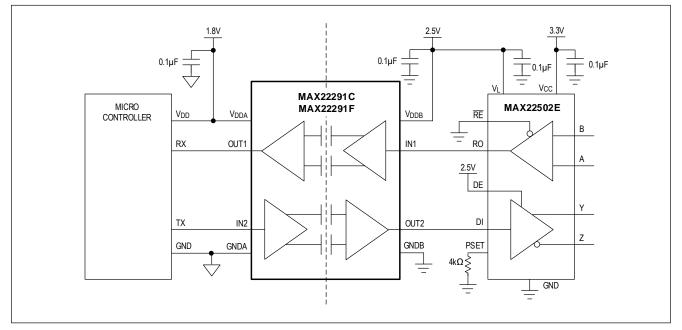
Table 4. Side A Supply Current Calculation Worksheet

SIDE A	V _{DDA} = 2.5V							
CHANNEL	IN/OUT	DATA RATE (Mbps)	LOAD TYPE	LOAD	NO LOAD CURRENT (mA)	LOAD CURRENT (mA)		
1	OUT	100	Capacitive	15pF	0.84	2.5V x 50MHz x 15pF = 1.875mA		
2	IN	20			0.35			
Total: 3.065mA								

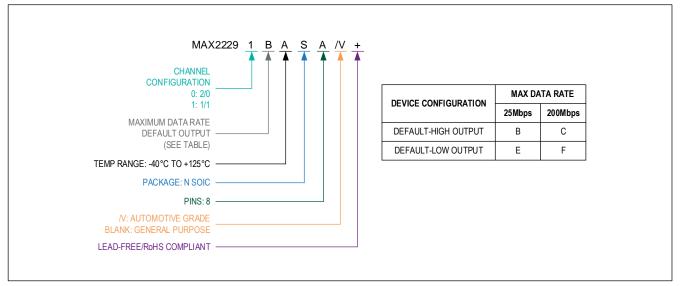
Table 5. Side B Supply Current Calculation Worksheet

SIDE B	V _{DDB} = 3.3V								
CHANNEL	IN/OUT DATA RATE (Mbps)		LOAD TYPE	LOAD	NO LOAD CURRENT (mA)	LOAD CURRENT (mA)			
1	IN	100			1.16				
2	OUT	20	Resistive	10kΩ	0.41	3.3V / 10kΩ x 0.5 = 0.165mA			
Total: 1.735mA									

Typical Application Circuits



Product Selector Guide



Ordering Information

PART NUMBER	CHANNEL CONFIGURATION	DATA RATE (Mbps)	DEFAULT OUTPUT	ISOLATION VOLTAGE (kV _{RMS})	TEMPERATURE RANGE	PIN-PACKAGE			
GENERAL PURPOSE DEVICES									
MAX22290BASA+*	2/0	25	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22290CASA+*	2/0	200	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22290EASA+*	2/0	25	Low	3	-40°C to +125°C	8 Narrow SOIC			
MAX22290FASA+*	2/0	200	Low	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291BASA+*	1/1	25	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291CASA+*	1/1	200	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291EASA+*	1/1	25	Low	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291FASA+*	1/1	200	Low	3	-40°C to +125°C	8 Narrow SOIC			
AUTOMOTIVE DEVICE	ES								
MAX22290BASA/V+*	2/0	25	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22290CASA/V+*	2/0	200	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22290EASA/V+*	2/0	25	Low	3	-40°C to +125°C	8 Narrow SOIC			
MAX22290FASA/V+*	2/0	200	Low	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291BASA/V+*	1/1	25	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291CASA/V+	1/1	200	High	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291EASA/V+	1/1	25	Low	3	-40°C to +125°C	8 Narrow SOIC			
MAX22291FASA/V+*	1/1	200	Low	3	-40°C to +125°C	8 Narrow SOIC			

*Future product—contact Maxim for availability.

+Denotes a lead(Pb)-free/RoHS-compliant package.

/V Denotes an automotive qualified part.

Chip Information

PROCESS: BICMOS